### **Electronic Devices and Circuit Theory**

**Boylestad** 

### FET Biasing Chapter 7

ALWAYS LEARNING



## **Common FET Biasing Circuits**

#### **JFET Biasing Circuits**

Fixed-Bias Self-Bias Voltage-Divider Bias

#### **D-Type MOSFET Biasing Circuits**

Self-Bias Voltage-Divider Bias

#### **E-Type MOSFET Biasing Circuits**

Feedback Configuration Voltage-Divider Bias

Electronic Devices and Circuit Theory Boylestad

### **Basic Current Relationships**

**For all FETs:**  $I_G \cong 0 \text{ A}$   $I_D = I_S$ 

For JFETS and D-Type MOSFETs:

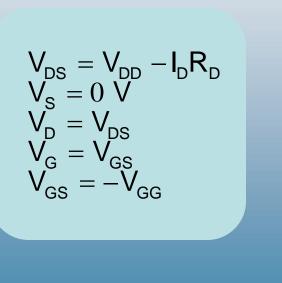
$$I_D = I_{DSS} \left( 1 - \frac{V_{GS}}{V_P} \right)^2$$

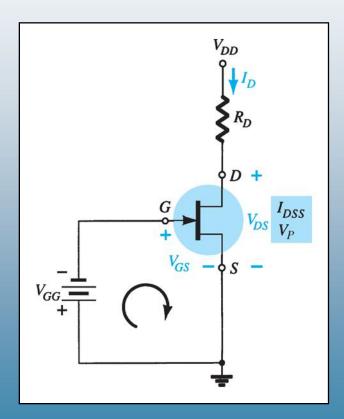
For E-Type MOSFETs:  
$$I_D = k(V_{GS} - V_T)^2$$

Electronic Devices and Circuit Theory Boylestad



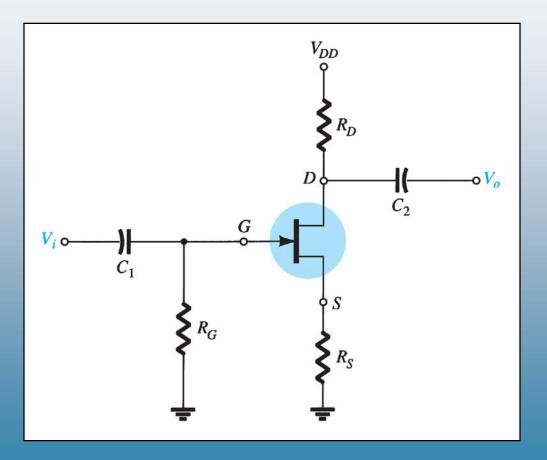
### **Fixed-Bias Configuration**





Electronic Devices and Circuit Theory Boylestad

### **Self-Bias Configuration**



Electronic Devices and Circuit Theory Boylestad

# **Self-Bias Calculations**

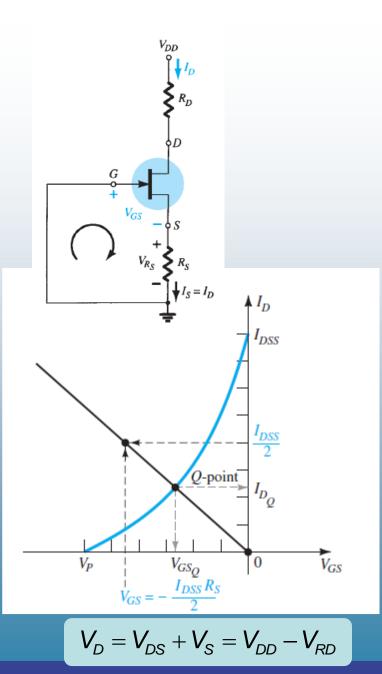
 $V_{\rm GS_Q} = -I_{\rm DQ}R_{\rm S}$ 

1. Select a value of  $I_D < I_{DSS}$  and use the component value of  $R_S$  to calculate  $V_{GS}$ . Plot the point identified by  $I_{DQ}$  and  $V_{GSQ}$  and draw a line from the origin of the axis to this point. 2. Plot the transfer curve using  $I_{DSS}$  and  $V_P$  $(V_P = |V_{GSoff}|$  on spec sheets) and a few points such as  $V_{GS} = V_P/4$  and  $V_{GS} = V_P/2$ etc.

The Q-point is located where the first line intersects the transfer curve. Using the value of I<sub>D</sub> at the Q-point (I<sub>DQ</sub>):

$$V_{DS} = V_{DD} - I_D(R_S + R_D)$$

$$V_{\rm S} = I_{\rm D} R_{\rm S}$$

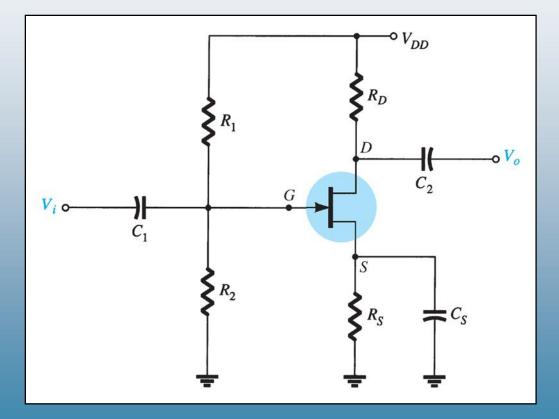


Electronic Devices and Circuit Theory Boylestad

### **Voltage-Divider Bias**

 $I_G = 0 \text{ A}$ 

 $I_D$  responds to changes in  $V_{GS}$ .



Electronic Devices and Circuit Theory Boylestad

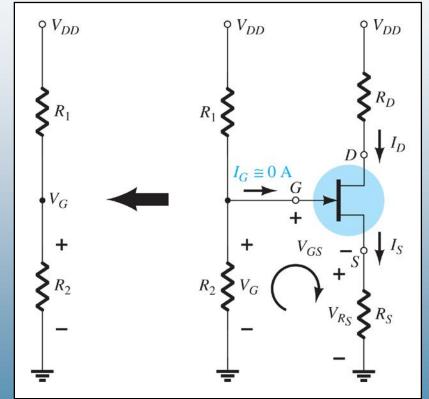
# **Voltage-Divider Bias Calculations**

 $V_G$  is equal to the voltage across divider resistor  $R_2$ :

$$V_G = \frac{R_2 V_{DD}}{R_1 + R_2}$$

Using Kirchhoff's Law:

$$V_{\rm GS} = V_{\rm G} - I_{\rm D} R_{\rm S}$$



# The Q-point is established by plotting a line that intersects the transfer curve.

Electronic Devices and Circuit Theory Boylestad

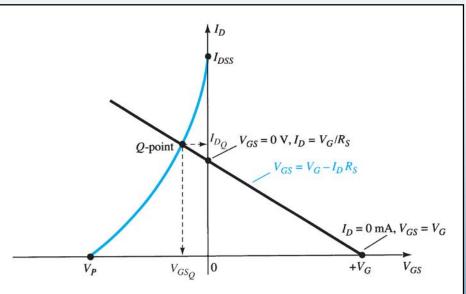
### **Voltage-Divider Q-Point**

Plot the line that is defined by these two points:

$$V_{GS} = V_G, \ I_D = 0 \text{ A}$$

$$V_{\rm GS} = 0$$
 V,  $I_D = V_G / R_S$ 

Plot the transfer curve by plotting  $I_{DSS}$ ,  $V_P$  and the calculated values of  $I_D$ 

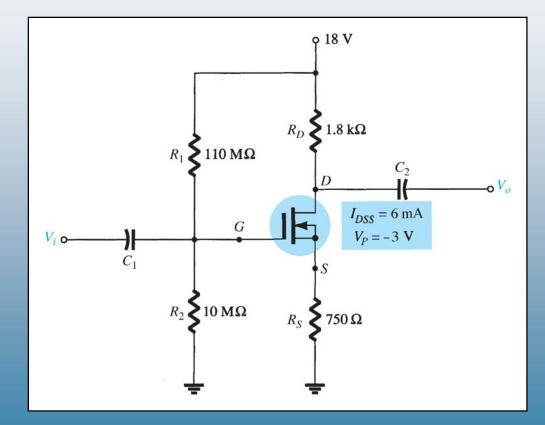


$$V_{DS} = V_{DD} - I_D (R_D + R_S)$$
$$V_D = V_{DD} - I_D R_D$$
$$V_S = I_D R_S$$

Electronic Devices and Circuit Theory Boylestad

# **D-Type MOSFET Bias Circuits**

Depletion-type MOSFET bias circuits are similar to those used to bias JFETs. The only difference is that D-type MOSFETs can operate with positive values of  $V_{GS}$  and with  $I_D$  values that exceed  $I_{DSS}$ .



### Self-Bias Q-Point (D-MOSFET)

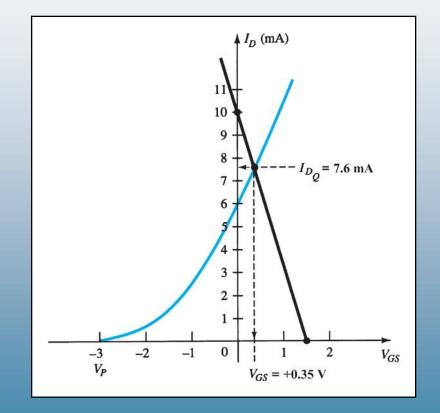
$$V_{\text{GS}} = -I_{\text{D}}R_{\text{S}}$$

Plot the line that is defined by these two points:

$$V_{GS} = V_G, I_D = 0 \text{ A}$$
$$I_D = V_G / R_S, V_{GS} = 0 \text{ V}$$

Plot the transfer curve using  $I_{DSS}$ ,  $V_P$  and calculated values of  $I_D$ .

The Q-point is located where the line intersects the transfer curve. Use the value of  $I_D$  at the Q-point to solve for the other circuit values.



#### These are the same steps used to analyze JFET self-bias circuits.

Electronic Devices and Circuit Theory Boylestad

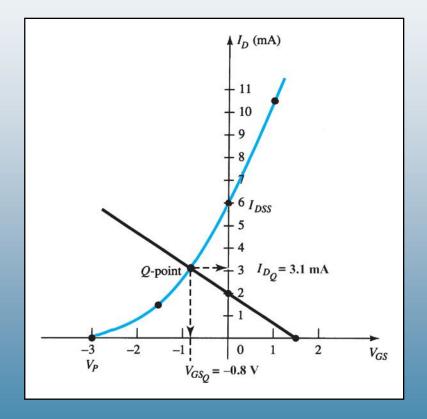
## Voltage-Divider Bias (D-MOSFET)

Plot the line that is defined by these two points:

 $V_{GS} = V_G, I_D = 0 A$  $I_D = V_G/R_S, V_{GS} = 0 V$ 

Plot the transfer curve using  $I_{DSS}$ ,  $V_P$  and calculated values of  $I_D$ .

The Q-point is located where the line intersects the transfer curve. Use the value of  $I_D$  at the Q-point to solve for the other variables in the circuit.

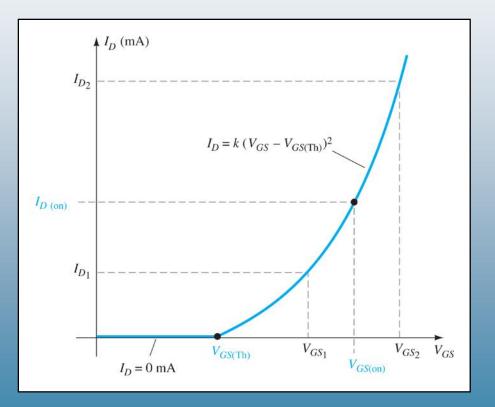


These are the same steps used to analyze JFET voltage-divider bias circuits.

Electronic Devices and Circuit Theory Boylestad

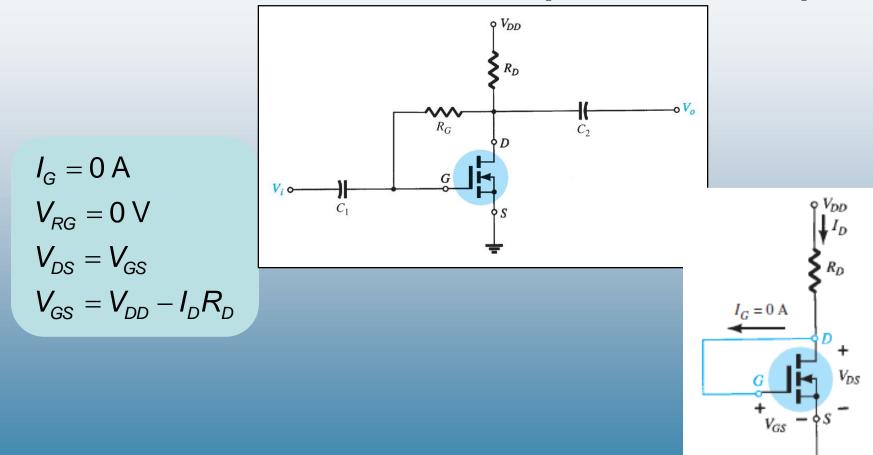
# **E-Type MOSFET Bias Circuits**

The transfer curve for the E-MOSFET is very different from that of a simple JFET or D-MOSFET.



Electronic Devices and Circuit Theory Boylestad

### Feedback Bias Circuit (E-MOSFET)



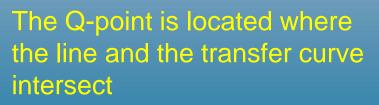
Electronic Devices and Circuit Theory Boylestad

### Feedback Bias Q-Point (E-MOSFET)

Plot the line that is defined by these two points:

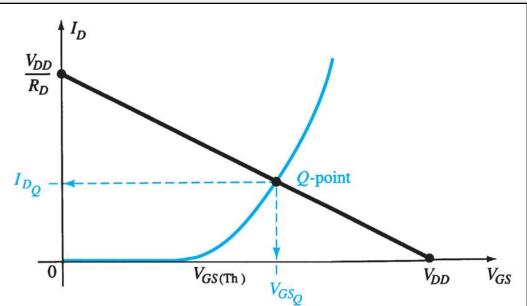
 $V_{GS} = V_{DD}, I_D = 0 \text{ A}$  $I_D = V_{DD} / R_D, V_{GS} = 0 \text{ V}$ 

Using these values from the spec sheet, plot the transfer curve:



Using the value of  ${\rm I}_{\rm D}$  at the Q-point, solve for the other variables in the circuit

Electronic Devices and Circuit Theory Boylestad



### **Voltage-Divider Biasing**

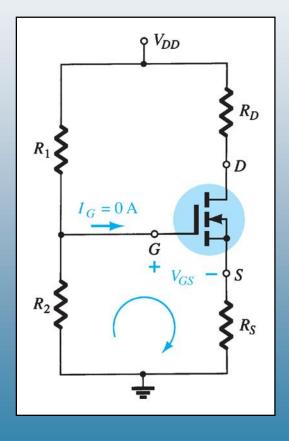
Plot the line and the transfer curve to find the Q-point using these equations:

$$V_{G} = \frac{R_{2}V_{DD}}{R_{1} + R_{2}}$$

$$V_{GS} = V_{G} - I_{D}R_{S}$$

$$V_{DS} = V_{DD} - V_{RS} - V_{RD}$$

$$V_{DS} = V_{DD} - I_{D}(R_{S} + R_{D})$$



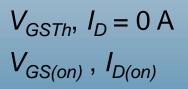
Electronic Devices and Circuit Theory Boylestad

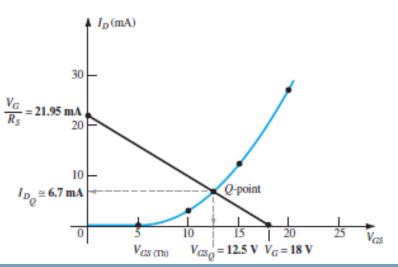
## Voltage-Divider Bias Q-Point (E-MOSFET)

Plot the line using

$$V_{GS} = V_G , I_D = 0 A$$
$$I_D = V_G / R_S , V_{GS} = 0 V$$

Using these values from the spec sheet plot the transfer curve:





The point where the line and the transfer curve intersect is the Q-point.

Using the value of  $I_D$  at the Q-point, solve for the other circuit values.

Electronic Devices and Circuit Theory Boylestad

### p-Channel FETs

For *p*-channel FETs the same calculations and graphs are used, except that the voltage polarities and current directions are reversed.

The graphs are mirror images of the *n*-channel graphs.

Electronic Devices and Circuit Theory Boylestad

### **Applications**

Voltage-controlled resistor JFET voltmeter Timer network Fiber optic circuitry MOSFET relay driver

Electronic Devices and Circuit Theory Boylestad